

CMPT3904E NPN
CMPT3906E PNP

**ENHANCED SPECIFICATION
SURFACE MOUNT SILICON
COMPLEMENTARY TRANSISTORS**



SOT-23 CASE

**MARKING CODE: CMPT3904E: C1AE
CMPT3906E: C2AE**

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

- ◆ **Collector-Base Voltage**
Collector-Emitter Voltage
- ◆ **Emitter-Base Voltage**
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT3904E and CMPT3906E are Enhanced versions of the CMPT3904 and CMPT3906 complementary switching transistors in a SOT-23 surface mount package, designed for small signal switching applications, interface circuit & driver circuit applications.

ENHANCED SPECIFICATIONS:

- ◆ BV_{CBO} from 40V min to 60V min. (CMPT3906E)
- ◆ BV_{EBO} from 5.0V min to 6.0V min. (CMPT3906E)
- ◆ $V_{CE(SAT)}$ from 0.3V max to 0.2V max. (CMPT3904E)
from 0.4V max to 0.2V max. (CMPT3906E)
- ◆ h_{FE} from 60 min to 70 min. (CMPT3904E) (CMPT3906E)

SYMBOL

		UNITS
V_{CBO}	60	V
V_{CEO}	40	V
V_{EBO}	6.0	V
I_C	200	mA
P_D	350	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	375	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	CMPT3904E		CMPT3906E		UNITS
		MIN	TYP	TYP	MAX	
I_{CEV}	$V_{CE}=30V, V_{EB}=3.0V$				50	nA
◆ BV_{CBO}	$I_C=10\mu A$	60	115	90		V
BV_{CEO}	$I_C=1.0mA$	40	60	55		V
◆ BV_{EBO}	$I_E=10\mu A$	6.0	7.5	7.9		V
◆ $V_{CE(SAT)}$	$I_C=10mA, I_B=1.0mA$		0.057	0.050	0.100	V
◆ $V_{CE(SAT)}$	$I_C=50mA, I_B=5.0mA$		0.100	0.100	0.200	V
$V_{BE(SAT)}$	$I_C=10mA, I_B=1.0mA$	0.65	0.75	0.75	0.85	V
$V_{BE(SAT)}$	$I_C=50mA, I_B=5.0mA$		0.85	0.85	0.95	V
◆ h_{FE}	$V_{CE}=1.0V, I_C=0.1mA$	90	240	130		
◆ h_{FE}	$V_{CE}=1.0V, I_C=1.0mA$	100	235	150		
h_{FE}	$V_{CE}=1.0V, I_C=10mA$	100	215	150	300	
◆ h_{FE}	$V_{CE}=1.0V, I_C=50mA$	70	110	120		
h_{FE}	$V_{CE}=1.0V, I_C=100mA$	30	50	55		

◆ Enhanced specification

R6 (15-September 2022)

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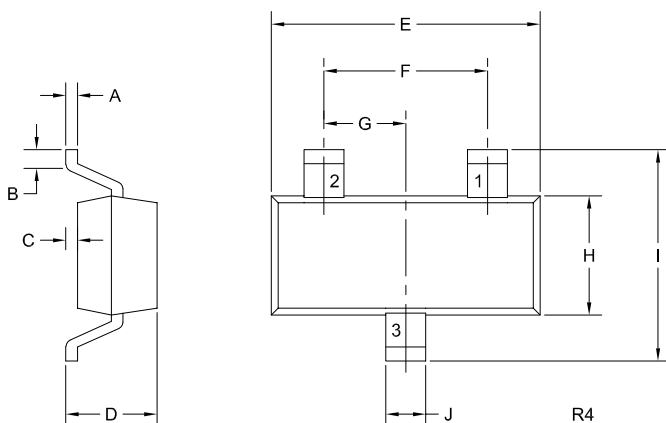
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ELECTRICAL CHARACTERISTICS - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
f_T	$V_{CE}=20\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	300		MHz
C_{ob}	$V_{CB}=5.0\text{V}$, $I_E=0$, $f=1.0\text{MHz}$		4.0	pF
C_{ib}	$V_{BE}=0.5\text{V}$, $I_C=0$, $f=1.0\text{MHz}$		12	pF
h_{ie}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	1.0	12	$k\Omega$
h_{re}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	0.1	10	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	100	400	
h_{oe}	$V_{CE}=10\text{V}$, $I_C=1.0\text{mA}$, $f=1.0\text{kHz}$	1.0	60	μS
NF	$V_{CE}=5.0\text{V}$, $I_C=100\mu\text{A}$, $R_S=1.0K\Omega$, $f=10\text{Hz}$ to 15.7kHz		4.0	dB
t_d	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$		35	ns
t_r	$V_{CC}=3.0\text{V}$, $V_{BE}=0.5\text{V}$, $I_C=10\text{mA}$, $I_{B1}=1.0\text{mA}$		35	ns
t_s	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		170	ns
t_f	$V_{CC}=3.0\text{V}$, $I_C=10\text{mA}$, $I_{B1}=I_{B2}=1.0\text{mA}$		80	ns

SOT-23 CASE - MECHANICAL OUTLINE



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.044	0.89	1.12
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.104	2.10	2.64
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R4)

LEAD CODE:

- 1) Base
- 2) Emitter
- 3) Collector

MARKING CODES:

CMPT3904E: C1AE
CMPT3906E: C2AE

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

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